

RJK4512DPP

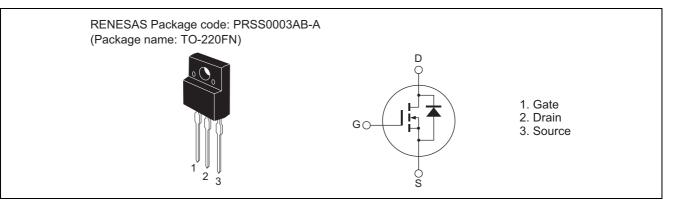
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1751-0100 Rev.1.00 Nov 12, 2008

Features

- Low on-resistance
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

		1 1	(1a - 25C)
Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	450	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D ^{Note4}	14	А
Drain peak current	I _{D (pulse)} Note1	42	A
Body-drain diode reverse drain current	I _{DR}	14	А
Body-drain diode reverse drain peak current	Note1 I _{DR (pulse)}	42	А
Avalanche current	I _{AP} ^{Note3}	3	А
Avalanche energy	E _{AR} ^{Note3}	0.5	mJ
Channel dissipation	Pch ^{Note2}	30	W
Channel to case thermal impedance	θch-c	4.17	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 $\mu s,$ duty cycle \leq 1%

2. Value at Tc = $25^{\circ}C$

3. STch = 25°C, Tch $\leq 150^{\circ}C$

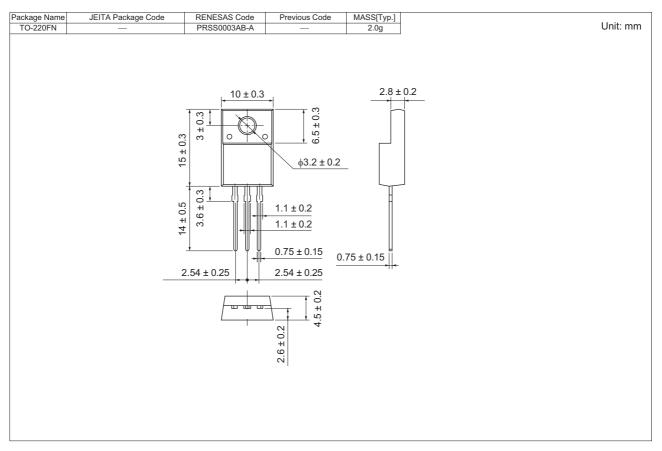
4. Limited by maximum safe operation area

Electrical Characteristics

	•		1	r		$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V _{(BR)DSS}	450		—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	_	—	1	μΑ	$V_{DS} = 450 \text{ V}, V_{GS} = 0$
Gate to source leak current	I _{GSS}	_	—	±0.1	μΑ	$V_{GS}=\pm 30~V,~V_{DS}=0$
Gate to source cutoff voltage	V _{GS(off)}	3.0		4.5	V	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R _{DS(on)}	_	0.43	0.51	Ω	$I_D = 7 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note5}}$
Input capacitance	Ciss	_	1100		pF	V _{DS} = 25 V
Output capacitance	Coss	_	125		pF	V _{GS} = 0 f = 1 MHz
Reverse transfer capacitance	Crss	_	15		pF	
Turn-on delay time	t _{d(on)}		30		ns	$ I_D = 7 A V_{GS} = 10 V R_L = 32.1 \Omega Rg = 10 \Omega $
Rise time	tr	_	25		ns	
Turn-off delay time	t _{d(off)}		78	_	ns	
Fall time	t _f		17	_	ns	
Total gate charge	Qg		29		nC	V _{DD} = 360 V
Gate to source charge	Qgs		5.5		nC	V _{GS} = 10 V I _D = 14 A
Gate to drain charge	Qgd	_	13		nC	
Body-drain diode forward voltage	V _{DF}	_	0.89	1.50	V	$I_F = 14 \text{ A}, V_{GS} = 0^{Note5}$
Body-drain diode reverse recovery time	t _{rr}		280	—	ns	$I_F = 14 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Notes: 5. Pulse test

Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK4512DPP-00-T2	1050 pcs	Box (Tube)

RenesasTechnology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

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Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510

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